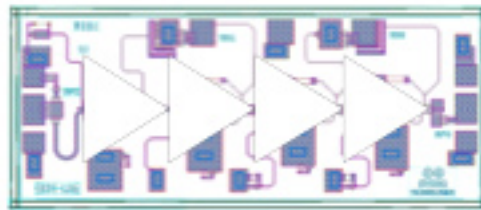


AMMC-6233

18 to 32 GHz GaAs Low Noise Amplifier



Data Sheet



Chip Size: 1900 x 800 μm (74.8 x 31.5 mils)
Chip Size Tolerance: $\pm 10 \mu\text{m}$ (± 0.4 mils)
Chip Thickness: 100 $\pm 10 \mu\text{m}$ (4 ± 0.4 mils)
RF Pad Dimensions: 110 x 90 μm (4.33 x 3.54 mils)
DC Pad Dimensions: 100 x 100 μm (3.94 x 3.94 mils)

Description

Avago Technologies' AMMC-6233 is a high gain, low-noise amplifier that operates from 18 GHz to 32 GHz. This LNA provides a wide-band solution for system design since it covers several bands, thus, reduces part inventory. The device has input / output match to 50 Ohm, is unconditionally stable and can be used as either primary or sub-sequential low noise gain stage. By eliminating the complex tuning and assembly processes typically required by hybrid (discrete- FET) amplifiers, the AMMC-6233 is a cost-effective alternative in the 18 - 32 GHz communications receivers. The backside of the chip is both RF and DC ground. This helps simplify the assembly process and reduces assembly related performance variations and costs. It is fabricated in a PHEMT process to provide exceptional noise and gain performance. For improved reliability and moisture protection, the die is passivated at the active areas.

Applications

- Microwave radio systems
- Satellite VSAT, DBS up/down link
- LMDS & Pt-Pt mmW long haul
- Broadband wireless access (including 802.16 and 802.20 WiMax)
- WLL and MMDS loops

Features

- Integrated DC block and choke
- 50 Ω input and output match
- Single positive supply
- No negative gate bias

Specifications ($V_d = 3.0 \text{ V}$, $I_{dd} = 65 \text{ mA}$)

- RF frequencies: 18 - 32 GHz
- Small-signal gain: 22 dB
- Low gain flatness: ± 1 dB
- Typical noise figure: 3.0 dB
- Typical output IP3: 19 dBm



Attention: Observe precautions for handling electrostatic sensitive devices.

ESD Machine Model (Class A)

ESD Human Body Model (Class 1A)

Refer to Avago Technologies Application Note A004R:

Electrostatic Discharge, Damage and Control.

Note:

1. This MMIC uses depletion mode pHEMT devices.

Absolute Maximum Ratings^[1]

Symbol	Parameters/Condition	Unit	Max
Vd	Drain to Ground Voltage	V	5.5
Id	Drain Current	mA	100
Pin	RF CW Input Power Max	dBm	10
Tch	Max Channel Temperature	C	+150
Tstg	Storage Temperature	C	-65 +150
Tmax	Maximum Assembly Temperature	C	260 for 20s

Note:

1. Operation in excess of any of these conditions may result in permanent damage to this device. The absolute maximum ratings for Vd, Id, and Pin were determined at an ambient temperature of 25°C unless noted otherwise.

DC Specifications/ Physical Properties^[2]

Symbol	Parameter and Test Condition	Unit	Min.	Typ.	Max.
Idd	Drain Current Under Any RF Power Drive and Temp.] (Vdd = 3 V)	mA		65	90
Vdd	Drain Supply Voltage	V		3	5
θjc	Thermal Resistance ^[3]	C/W		27	

Notes:

2. Ambient operational temperature TA = 25°C unless noted
3. Channel-to-backside Thermal Resistance (Tchannel = 34°C) as measured using infrared microscopy. Thermal Resistance at backside temp. (Tb) = 25°C calculated from measured data.

AMMC-6233 RF Specifications^[4]

TA = 25°C, Vdd = 3.0 V, Id = 65 mA, Zo = 50 Ω

Symbol	Parameters and Test Conditions	Frequencies (GHz)	Units	Minimum	Typical	Maximum
Gain	RF Small Signal Gain	18, 26, 31	dB	18	22	
NF	Noise Figure into 50W(5)	18, 26, 31	dB		3.0	4.0
RLin	Input Return Loss		dB		-12	
RLout	Output Return Loss		dB		-12	
Iso	Isolation		dB		-45	
P-1dB	Output Power at 1dB ⁽⁷⁾ Gain Compression		dBm		8	
OIP3	Output Third Order Intercept Point		dBm		19	

Notes:

4. All tested parameters guaranteed with measurement accuracy +/-0.5 dB for the 6 to 20 GHz range, ±0.75 dB for the 20 to 33 GHz range and ±1.0 dB for the 33 to 50 GHz range.
5. NF is measured on-wafer. Additional bond wires (~0.2 nH) at input could improve NF at some frequencies.

AMMC-6233 Typical Performances

($T_A = 25^\circ\text{C}$, $V_{dd} = 3.0\text{ V}$, $I_{total} = 65\text{ mA}$, $Z_{in} = Z_{out} = 50\ \Omega$ unless otherwise stated)

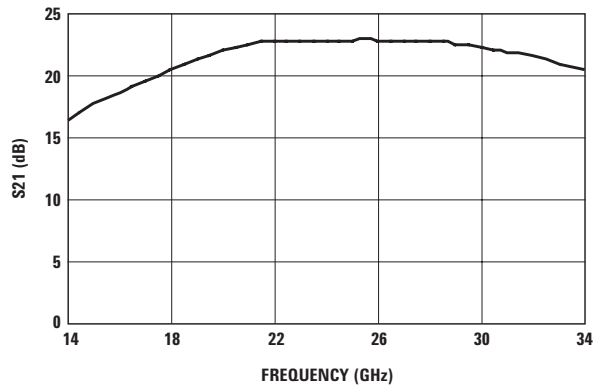


Figure 1. Typical gain

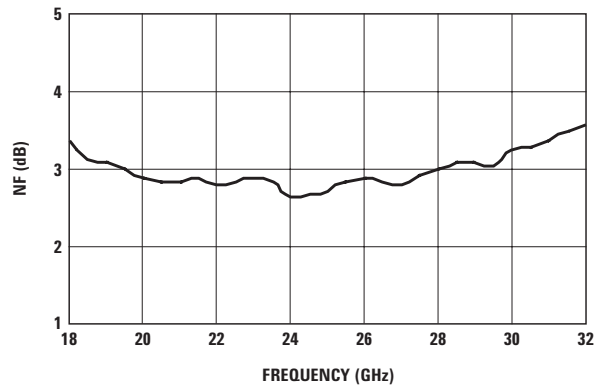


Figure 2. Typical noise figure

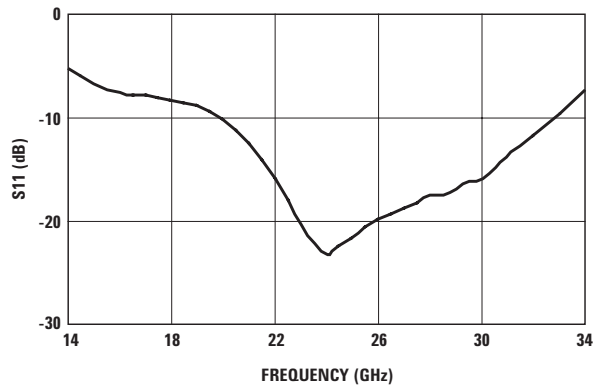


Figure 3. Typical input return loss

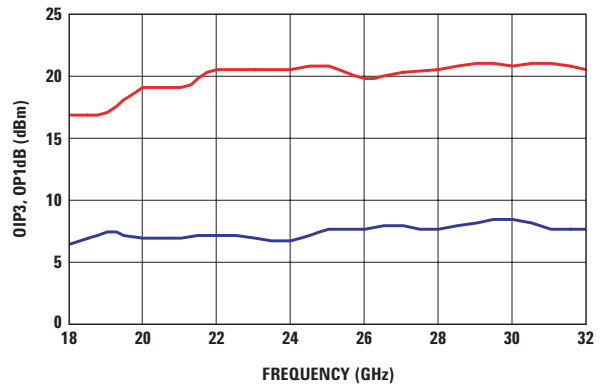


Figure 4. Typical output P-1dB

AMMC-6233 Typical Performances (Cont'd.)

($T_A = 25^\circ\text{C}$, $V_{dd} = 3.0\text{ V}$, $I_{total} = 65\text{ mA}$, $Z_{in} = Z_{out} = 50\ \Omega$ unless otherwise stated)

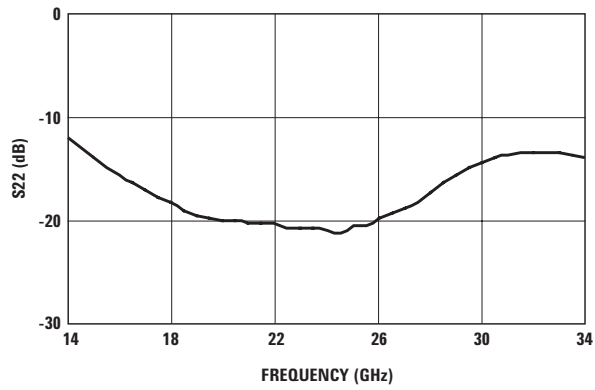


Figure 5. Typical output return loss

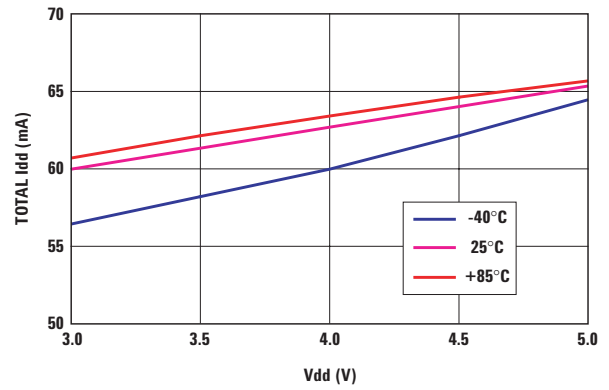


Figure 6. Total Idd over temp vs. Vdd

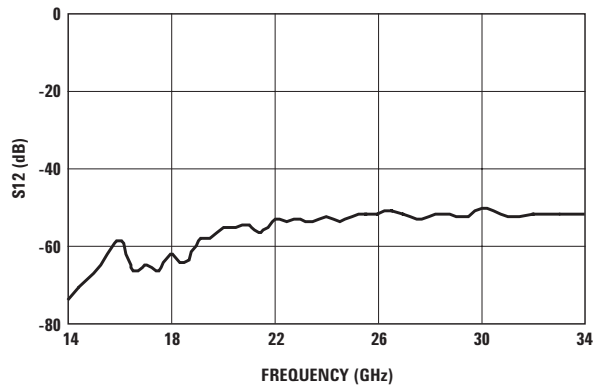


Figure 7. Typical isolation

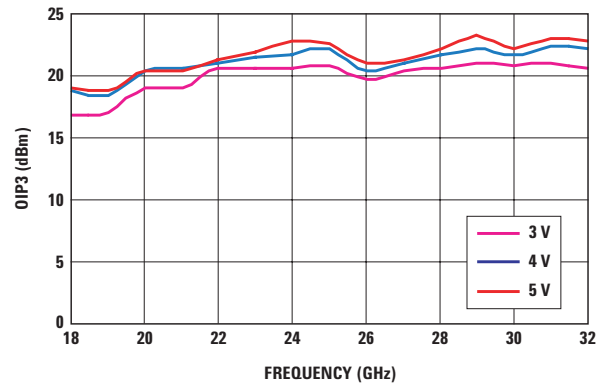


Figure 8. Typical output IP3 over Vdd

AMMC-6233 Typical Performances (Cont'd.)

($T_A = 25^\circ\text{C}$, $V_{dd} = 3.0\text{ V}$, $I_{total} = 65\text{ mA}$, $Z_{in} = Z_{out} = 50\ \Omega$ unless otherwise stated)

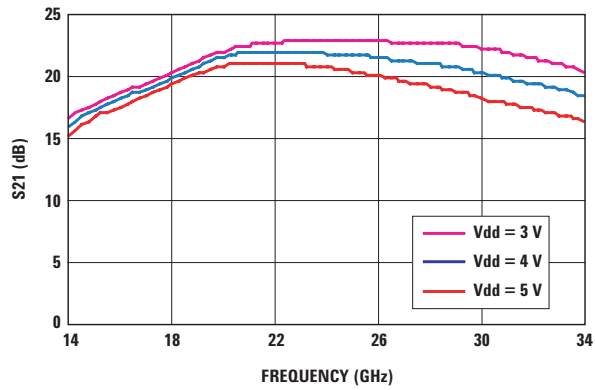


Figure 9. Typical gain over V_{dd}

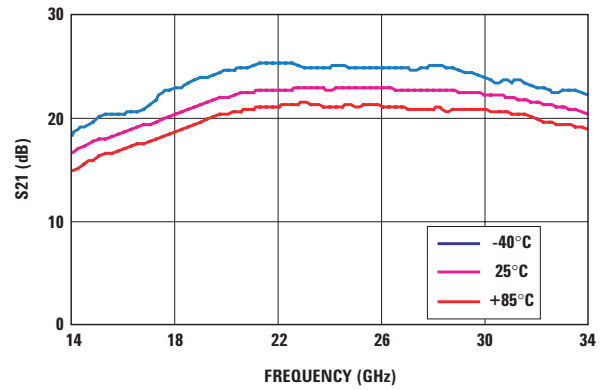


Figure 10. Typical gain over temp

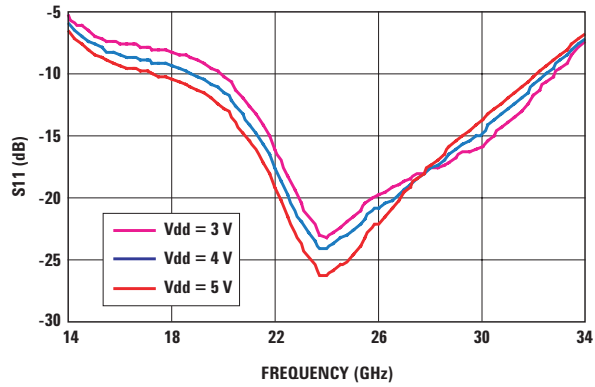


Figure 11. Typical input return loss over V_{dd}

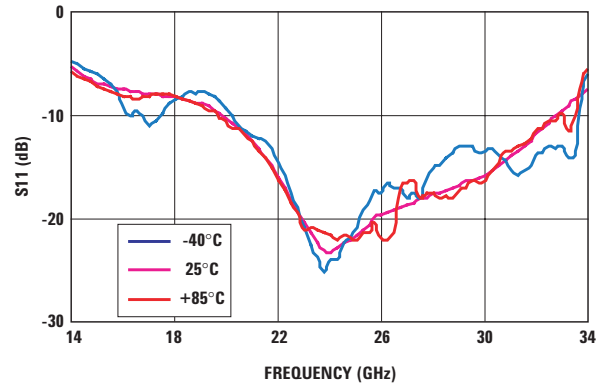


Figure 12. Typical input return loss over temp

AMMC-6233 Typical Performances (Cont'd.)

($T_A = 25^\circ\text{C}$, $V_{dd} = 3.0\text{ V}$, $I_{total} = 65\text{ mA}$, $Z_{in} = Z_{out} = 50\ \Omega$ unless otherwise stated)

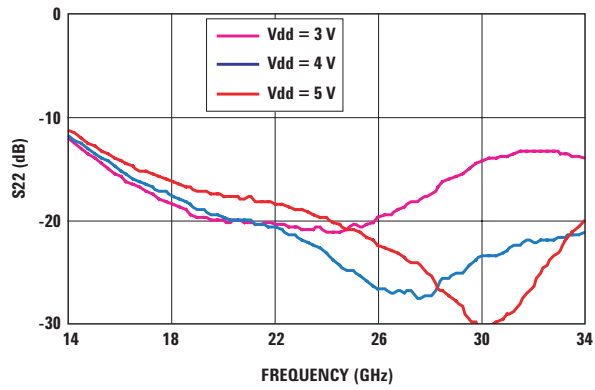


Figure 13. Typical output return loss over Vdd.

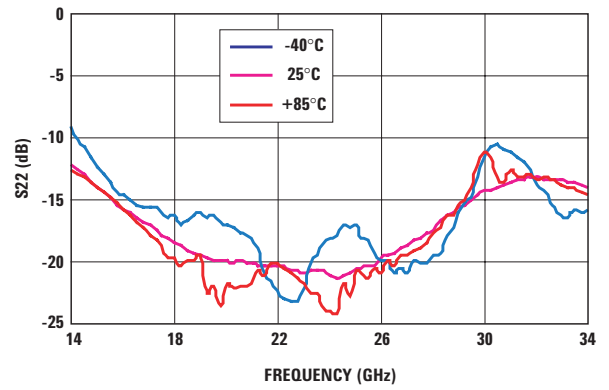


Figure 14. Typical output return loss over temp

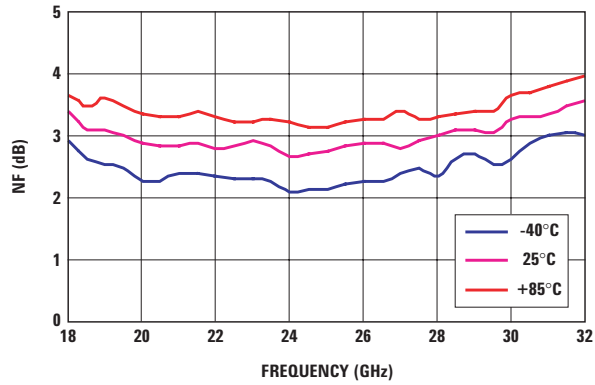


Figure 15. Typical noise figure over temp

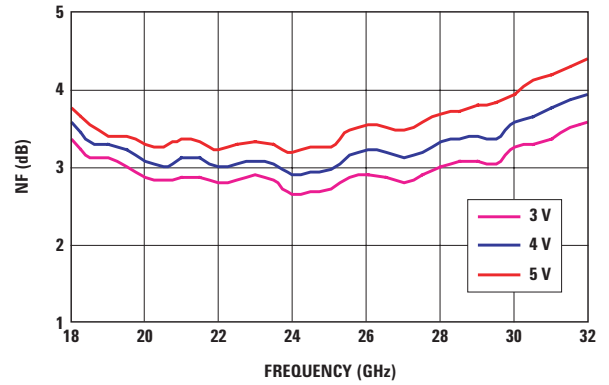


Figure 16. Typical noise figure over Vdd

Biasing and Operation

The AMMC-6233 is normally biased with a positive supply connected to both VD1 and VD2 bond pads through the 100pF bypass capacitor as shown in Figure 19. The recommended supply voltage is 3 V. It is important to place the bypass capacitor as close to the die as possible. No negative gate bias voltage is needed for the AMMC-6233. Input and output 50-ohm match are achieved on-chip; therefore no other external component is required at the input or output. In addition, the input and output are DC-blocked with internal coupling capacitors.

No ground wires are needed because all ground connections are made with plated through-holes to the backside of the device.

Refer the Absolute Maximum Ratings table for allowed DC and thermal conditions.

Assembly Techniques

The backside of the MMIC chip is RF ground. For microstrip applications the chip should be attached directly to the ground plane (e.g. circuit carrier or heatsink) using electrically conductive epoxy. [1,2]

For best performance, the topside of the MMIC should be brought up to the same height as the circuit surrounding it. This can be accomplished by mounting a gold plate metal shim (same length and width as the MMIC) under the chip which is of correct thickness to make the chip and adjacent circuit the same height. The amount of epoxy used for the chip and/or shim attachment should be just enough to provide a thin fillet around the bottom perimeter of the chip or shim. The ground plan should be free of any residue that may jeopardize electrical or mechanical attachment.

The location of the RF bond pads is shown in Figure 12. Note that all the RF input and output ports are in a Ground-Signal-Ground configuration.

RF connections should be kept as short as reasonable to minimize performance degradation due to undesirable series inductance. A single bond wire is normally sufficient for signal connections, however double bonding with 0.7 mil gold wire or use of gold mesh is recommended for best performance, especially near the high end of the frequency band.

Thermosonic wedge bonding is preferred method for wire attachment to the bond pads. Gold mesh can be attached using a 2 mil round tracking tool and a tool force of approximately 22 grams and a ultrasonic power of roughly 55 dB for a duration of 76 ± 8 mS. The guided wedge at an ultrasonic power level of 64 dB can be used for 0.7 mil wire. The recommended wire bond stage temperature is 150 ± 2 C.

Caution should be taken to not exceed the Absolute Maximum Rating for assembly temperature and time.

The chip is 100um thick and should be handled with care. This MMIC has exposed air bridges on the top surface and should be handled by the edges or with a custom collet (do not pick up the die with a vacuum on die center).

This MMIC is also static sensitive and ESD precautions should be taken.

Notes:

1. Ablebond 84-1 LM1 silver epoxy is recommended.
2. Eutectic attach is not recommended and may jeopardize reliability of the device.

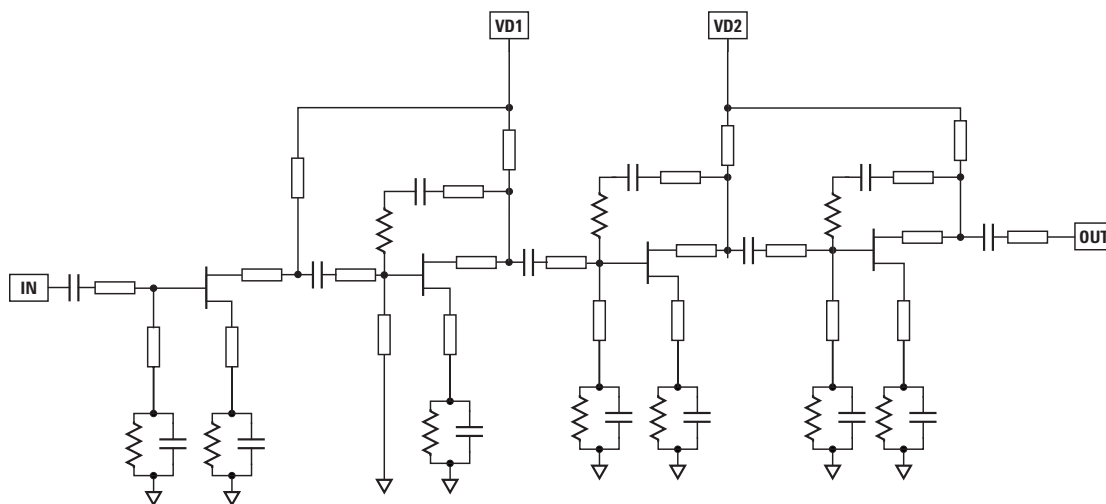


Figure 17. AMMC-6233 simplified schematic

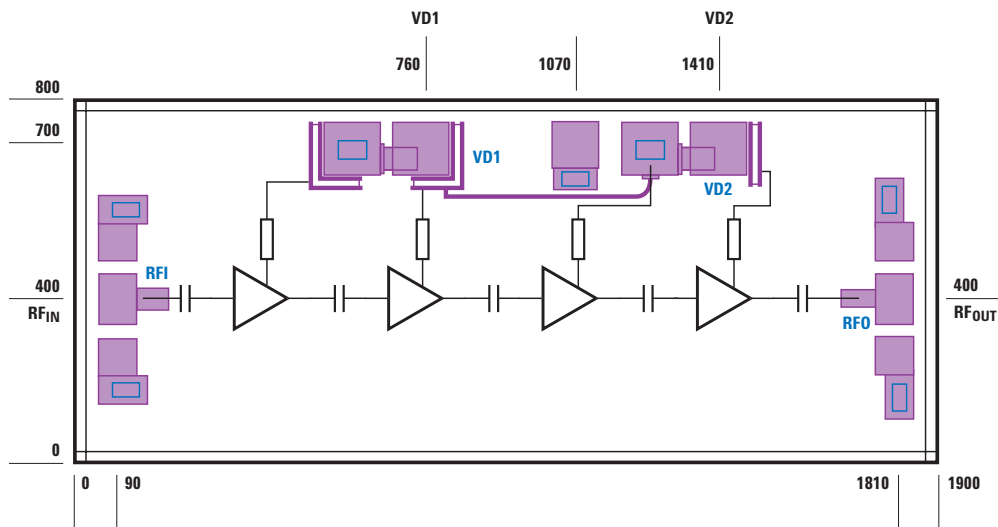


Figure 18. AMMC-6233 bonding pad locations

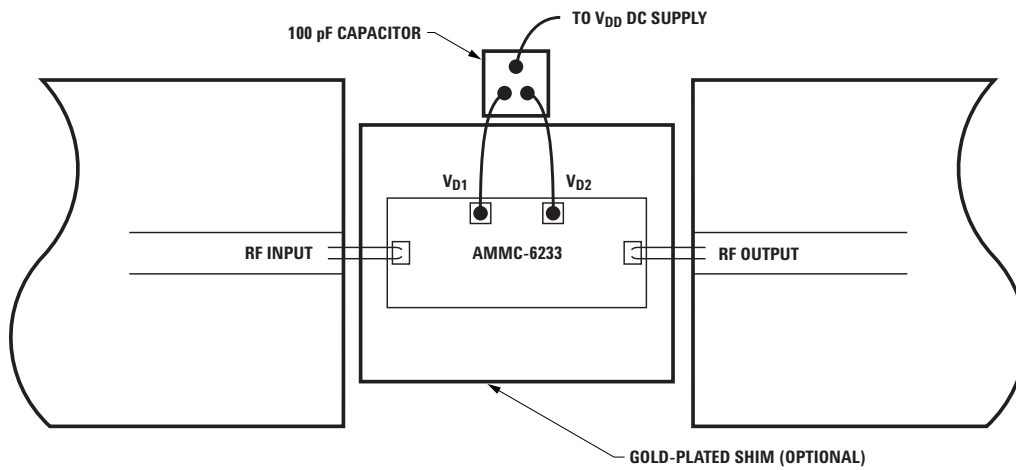


Figure 19. AMMC-6233 assembly diagram

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